INTEL Docket No.: P18062

Patent

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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	<i>,</i>
In re Application of: KESHAVARZI et al.	Examiner: Not yet assigned
Serial No.: Not yet assigned) Group Art Unit: Not yet assigned
Filing Date: Herewith	INTEL Docket No.: P18062
FOR: ASYMMETRIC MEMORY CELL))
)

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Applicants submit herewith patents, publications or other information of which they are aware that they believe may be material to the examination of this application, and in respect of which, there may be a duty to disclose.

The filing of this information disclosure statement shall not be construed as a representation that a thorough search has been made, an admission that the information cited is, or is considered to be, material to patentability, or that no other material information exists. Nor shall the filing of this information disclosure statement be construed as an admission against interest in any manner.

This Information Disclosure Statement is filed in accordance with 37 CFR §§1.56, 1.97 and 1.98. The items listed on the accompanying Form PTO-1449 may be deemed to be pertinent to the above-identified application and are made of record to assist the Patent and Trademark Office in its examination of this application. The Examiner is respectfully requested to fully consider the items listed on the enclosed copy of Form PTO-1449 and to independently ascertain their teaching.

No fee is believed to be due under 37 CFR §1.17(p) for this Information Disclosure Statement since it is being filed concurrently with the above-identified application.

Respectfully submitted,

December 31, 2003
Date

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE		Complete if Known			
		Applicati n Numb r	Not yet assigned		
		Filing Dat	Herewith		
STATEMENT BY APPLICANT		First Named Inventor	KESHAVARZI, Ali		
				Group Art Unit	Not yet assigned
(use as many sheets as necessary)		Examiner Name	Not yet assigned		
Sheet	1	of	1	INTEL Docket Number	P18062

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²	
	A	Ohsawa, Takashi et al., "Memory Design Using a One-Transistor Gain Cell on SOI, IEEE Journal of Solid-State Circuits, Vol. 37, No. 11, November 2002, ISSN: 0018-9200, pp. 1510-1522.		
	В	Thompson, Scott, et al., "MOS Scaling: Transistor Challenges for the 21st Century", Intel Technology Journal Q3'98. 19pgs.		
	C.	Ohsawa, Takashi et al., "ISSCC 2002/Session 9/Dram and Ferroelectric Memories / 9.1", Memory LSI Research and Development Center, Yokohama, Japan. 3pgs.		
	D	Brand, A., "Intel's 0.25 Micron, 2.0Volts Logic Process Technology", Intel Technology Journal Q3'98. 9pgs.		

Examiner	Date	
Signature	Considered	

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²Applicant is to place a check mark here if English language Translation is attached.